ADG608/ADG609–SPECIFICATIONS

DUAL SUPPLY[1] (V_{DD} = +5 V ± 10%, V_{SS} = –5 V ± 10%, GND = 0 V, unless otherwise noted)

Parameter	B Version +25°C	B Version –40°C to +85°C	T Version +25°C	T Version –55°C to +125°C	Units	Test Conditions/ Comments
ANALOG SWITCH						
Analog Signal Range		V_{SS} to V_{DD}		V_{SS} to V_{DD}	V	
R_{ON}	22		22		Ω typ	–3.5 V ≤ V_S ≤ +3.5 V, I_S = –1 mA;
	30	35	30	40	Ω max	V_{DD} = +4.5 V, V_{SS} = –4.5 V; Test Circuit 1
ΔR_{ON}	5	6	5	6	Ω max	–3 V ≤ V_S ≤ +3 V, I_{DS} = –1 mA; V_{DD} = +5 V, V_{SS} = –5 V
R_{ON} Match	2	3	2	3	Ω max	V_S = 0 V, I_{DS} = –1 mA; V_{DD} = +5 V, V_{SS} = –5 V
LEAKAGE CURRENTS						V_{DD} = +5.5 V, V_{SS} = –5.5 V
Source OFF Leakage I_S (OFF)	±0.05		±0.05		nA typ	V_D = ±4.5 V, V_S = ∓4.5 V;
	±0.5	±2	±0.5	±10	nA max	Test Circuit 2
Drain OFF Leakage I_D (OFF)	±0.05		±0.05		nA typ	V_D = ±4.5 V, V_S = ∓4.5 V;
ADG608	±0.5	±2	±0.5	±10	nA max	Test Circuit 3
ADG609	±0.5	±1	±0.5	±5	nA max	
Channel ON Leakage I_D, I_S (ON)	±0.05		±0.05		nA typ	V_S = V_D = ±4.5 V;
ADG608	±0.5	±3	±0.5	±20	nA max	Test Circuit 4
ADG609	±0.5	±1.5	±0.5	±10	nA max	
DIGITAL INPUTS						
Input High Voltage, V_{INH}		2.4		2.4	V min	
Input Low Voltage, V_{INL}		0.8		0.8	V max	
Input Current						
I_{INL} or I_{INH}		±1		±1	µA max	V_{IN} = 0 or V_{DD}
C_{IN}, Digital Input Capacitance	5		5		pF typ	
DYNAMIC CHARACTERISTICS[2]						
$t_{TRANSITION}$	50		50		ns typ	R_L = 300 Ω, C_L = 35 pF;
	75	90	75	100	ns max	V_{S1} = ±3.5 V, V_{S8} = ∓3.5 V; Test Circuit 5
t_{OPEN}	10		10		ns min	R_L = 300 Ω, C_L = 35 pF; V_S = +3.5 V; Test Circuit 6
t_{ON} (EN)	50		50		ns typ	R_L = 300 Ω, C_L = 35 pF;
	75	90	75	100	ns max	V_S = +3.5 V; Test Circuit 7
t_{OFF} (EN)	30		30		ns typ	R_L = 300 Ω, C_L = 35 pF;
	45	60	45	75	ns max	V_S = +3.5 V; Test Circuit 7
Charge Injection	6		6		pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF; Test Circuit 8
OFF Isolation	85		85		dB typ	R_L = 1 kΩ, C_L = 15 pF, f = 100 kHz; V_S = 3 V rms; Test Circuit 9
Channel-to-Channel Crosstalk	85		85		dB typ	R_L = 1 kΩ, C_L = 15 pF, f = 100 kHz; Test Circuit 10
C_S (OFF)	9		9		pF typ	
C_D (OFF)						
ADG608	40		40		pF typ	
ADG609	20		20		pF typ	
C_D (ON)						
ADG608	54		54		pF typ	
ADG609	34		34		pF typ	
POWER REQUIREMENTS						
I_{DD}	0.05	0.2	0.05	0.2	µA typ	V_{IN} = 0 V or V_{DD}
	0.2	2	0.2	2	µA max	
I_{SS}	0.01	0.1	0.01	0.1	µA typ	
	0.1	1	0.1	1	µA max	

NOTES
[1]Temperature ranges are as follows: B Version: –40°C to +85°C; T Version: –55°C to +125°C.
[2]Guaranteed by design, not subject to production test.
Specifications subject to change without notice.

SINGLE SUPPLY[1] (V_{DD} = +5 V ± 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted)

Parameter	B Version +25°C	B Version –40°C to +85°C	T Version +25°C	T Version –55°C to +125°C	Units	Test Conditions/ Comments
ANALOG SWITCH						
Analog Signal Range		0 to V_{DD}		0 to V_{DD}	V	
R_{ON}	40		40		Ω typ	V_S = +3.5 V, I_S = –1 mA;
	50	60	50	70	Ω max	V_{DD} = +4.5 V; Test Circuit 1
ΔR_{ON}	5	6	5	6	Ω max	+1 V ≤ V_S ≤ +3 V, I_{DS} = –1 mA; V_{DD} = +5 V
R_{ON} Match	2	3	2	3	Ω max	V_S = 0 V, I_{DS} = –1 mA; V_{DD} = +5 V
LEAKAGE CURRENTS						V_{DD} = +5.5 V
Source OFF Leakage I_S (OFF)	±0.05		±0.05		nA typ	V_D = 4.5 V/0.1 V, V_S = 0.1 V/4.5 V;
	±0.5	±2	±0.5	±10	nA max	Test Circuit 2
Drain OFF Leakage I_D (OFF)	±0.05		±0.05		nA typ	V_D = 4.5 V/0.1 V, V_S = 0.1 V/4.5 V;
ADG608	±0.5	±2	±0.5	±10	nA max	Test Circuit 3
ADG609	±0.5	±1	±0.5	±5	nA max	
Channel ON Leakage I_D, I_S (ON)	±0.05		±0.05		nA typ	V_S = V_D = 4.5 V/0.1 V;
ADG608	±0.5	±3	±0.5	±20	nA max	Test Circuit 4
ADG609	±0.5	±1.5	±0.5	±10	nA max	
DIGITAL INPUTS						
Input High Voltage, V_{INH}		2.4		2.4	V min	
Input Low Voltage, V_{INL}		0.8		0.8	V max	
Input Current						
I_{INL} or I_{INH}		±1		±1	µA max	V_{IN} = 0 or V_{DD}
C_{IN}, Digital Input Capacitance	5		5		pF typ	
DYNAMIC CHARACTERISTICS[2]						
$t_{TRANSITION}$	80		80		ns typ	R_L = 300 Ω, C_L = 35 pF;
	100	130	100	150	ns max	V_{S1} = 3.5 V/0 V, V_{S8} = 0 V/3.5 V; Test Circuit 5
t_{OPEN}	10		10		ns min	R_L = 300 Ω, C_L = 35 pF; V_S = +3.5 V; Test Circuit 6
t_{ON} (EN)	80		80		ns typ	R_L = 300 Ω, C_L = 35 pF;
	100	130	100	150	ns max	V_S = +3.5 V; Test Circuit 7
t_{OFF} (EN)	40		40		ns typ	R_L = 300 Ω, C_L = 35 pF;
	50	60	50	75	ns max	V_S = +3.5 V; Test Circuit 7
Charge Injection	0.5		0.5		pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF;
	3		3		pC max	Test Circuit 8
OFF Isolation	85		85		dB typ	R_L = 1 kΩ, C_L = 15 pF, f = 100 kHz; V_S = 1.5 V rms; Test Circuit 9
Channel-to-Channel Crosstalk	85		85		dB typ	R_L = 1 kΩ, C_L = 15 pF, f = 100 kHz; Test Circuit 10
C_S (OFF)	9		9		pF typ	
C_D (OFF)						
ADG608	40		40		pF typ	
ADG609	20		20		pF typ	
C_D (ON)						
ADG608	54		54		pF typ	
ADG609	34		34		pF typ	
POWER REQUIREMENTS						
I_{DD}	0.05	0.2	0.05	0.2	µA typ	V_{IN} = 0 V or V_{DD}
	0.2	2	0.2	2	µA max	

NOTES
[1]Temperature ranges are as follows: B Version: –40°C to +85°C; T Version: –55°C to +125°C.
[2]Guaranteed by design, not subject to production test.
Specifications subject to change without notice.

ADG608/ADG609–SPECIFICATIONS

SINGLE SUPPLY[1] (V_{DD} = +3.3 V ± 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted)

Parameter	B Version +25°C	B Version –40°C to +85°C	T Version +25°C	T Version –55°C to +125°C	Units	Test Conditions/ Comments
ANALOG SWITCH						
Analog Signal Range		0 to V_{DD}		0 to V_{DD}	V	
R_{ON}	60		60		Ω typ	V_S = +1.5 V, I_S = –1 mA;
	90	100	90	120	Ω max	V_{DD} = +3 V; Test Circuit 1
R_{ON} Match	3	3	3	3	Ω max	V_S = 0 V, I_{DS} = –1 mA, V_{DD} = +3.3 V
LEAKAGE CURRENTS						V_{DD} = +3.6 V
Source OFF Leakage I_S (OFF)	±0.05		±0.05		nA typ	V_D = 2.6 V/0.1 V, V_S = 0.1 V/2.6 V;
	±0.5	±2	±0.5	±10	nA max	Test Circuit 2
Drain OFF Leakage I_D (OFF)	±0.05		±0.05		nA typ	V_D = 2.6 V/0.1 V, V_S = 0.1 V/2.6 V;
ADG608	±0.5	±2	±0.5	±10	nA max	Test Circuit 3
ADG609	±0.5	±1	±0.5	±5	nA max	
Channel ON Leakage I_D, I_S (ON)	±0.05		±0.05		nA typ	V_S = V_D = 2.6 V/0.1 V;
ADG608	±0.5	±3	±0.5	±20	nA max	Test Circuit 4
ADG609	±0.5	±1.5	±0.5	±10	nA max	
DIGITAL INPUTS						
Input High Voltage, V_{INH}		2.4		2.4	V min	
Input Low Voltage, V_{INL}		0.8		0.8	V max	
Input Current						
I_{INL} or I_{INH}		±1		±1	μA max	V_{IN} = 0 or V_{DD}
C_{IN}, Digital Input Capacitance	5		5		pF typ	
DYNAMIC CHARACTERISTICS[2]						
$t_{TRANSITION}$	120		120		ns typ	R_L = 300 Ω, C_L = 35 pF;
	170	225	170	250	ns max	V_{S1} = 1.5 V/0 V, V_{S8} = 0 V/1.5 V; Test Circuit 5
t_{OPEN}	10		10		ns min	R_L = 300 Ω, C_L = 35 pF; V_S = +1.5 V; Test Circuit 6
t_{ON} (EN)	120		120		ns typ	R_L = 300 Ω, C_L = 35 pF;
	170	225	170	250	ns max	V_S = +1.5 V; Test Circuit 7
t_{OFF} (EN)	40		40		ns typ	R_L = 300 Ω, C_L = 35 pF;
	60	75	60	90	ns max	V_S = +1.5 V; Test Circuit 7
Charge Injection	0.5		0.5		pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF;
	3		3		pC max	Test Circuit 8
OFF Isolation	85		85		dB typ	R_L = 1 kΩ, C_L = 15 pF, f = 100 kHz; V_S = 1 V rms; Test Circuit 9
Channel-to-Channel Crosstalk	85		85		dB typ	R_L = 1 kΩ, C_L = 15 pF, f = 100 kHz; Test Circuit 10
C_S (OFF)	9		9		pF typ	
C_D (OFF)						
ADG608	40		40		pF typ	
ADG609	20		20		pF typ	
C_D (ON)						
ADG608	54		54		pF typ	
ADG609	34		34		pF typ	
POWER REQUIREMENTS						
I_{DD}	0.05	0.2	0.05	0.2	μA typ	V_{IN} = 0 V or V_{DD}
	0.2	2	0.2	2	μA max	

NOTES
[1]Temperature ranges are as follows: B Version: –40°C to +85°C; T Version: –55°C to +125°C.
[2]Guaranteed by design, not subject to production test.
Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS[1]

(T_A = +25°C unless otherwise noted)

V_{DD} to V_{SS} . . . . . +13 V
V_{DD} to GND . . . . . –0.3 V to +6.5 V
V_{SS} to GND . . . . . +0.3 V to –6.5 V
Analog, Digital Inputs[2] . . . . . –0.3 V to V_{DD} + 2 V
or 20 mA, Whichever Occurs First
Continuous Current, S or D . . . . . 20 mA
Peak Current, S or D
(Pulsed at 1 ms, 10% Duty Cycle Max) . . . . . 40 mA
Operating Temperature Range
Industrial (B Version) . . . . . –40°C to +85°C
Extended (T Version) . . . . . –55°C to +125°C
Storage Temperature Range . . . . . –65°C to +150°C
Junction Temperature . . . . . +150°C
Plastic DIP Package
θ_{JA}, Thermal Impedance . . . . . 117°C/W
Lead Temperature, Soldering (10 sec) . . . . . +260°C
SOIC Package
θ_{JA}, Thermal Impedance . . . . . 77°C/W
Lead Temperature, Soldering
Vapor Phase (60 sec) . . . . . +215°C
Infrared (15 sec) . . . . . +220°C
TSSOP Package
θ_{JA}, Thermal Impedance . . . . . 158°C/W
Lead Temperature, Soldering
Vapor Phase (60 sec) . . . . . +215°C
Infrared (15 sec) . . . . . +220°C
ESD Rating . . . . . >5000 V

NOTES

[1]Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

[2]Overvoltages at A, S, D or EN will be clamped by internal diodes. Current should be limited to the maximum ratings given.

Table I. ADG608 Truth Table

A2	A1	A0	EN	ON SWITCH
X	X	X	0	NONE
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

X = Don't Care

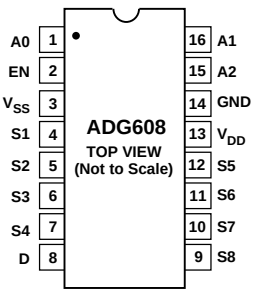
Table II. ADG609 Truth Table

A1	A0	EN	ON SWITCH PAIR
X	X	0	NONE
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

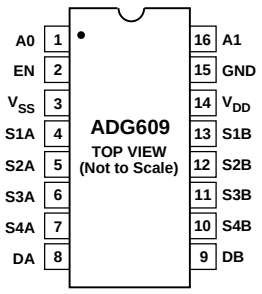
X = Don't Care

PIN CONFIGURATIONS

DIP/SOIC/TSSOP



DIP/SOIC/TSSOP



ADG608/ADG609–Typical Performance Characteristics

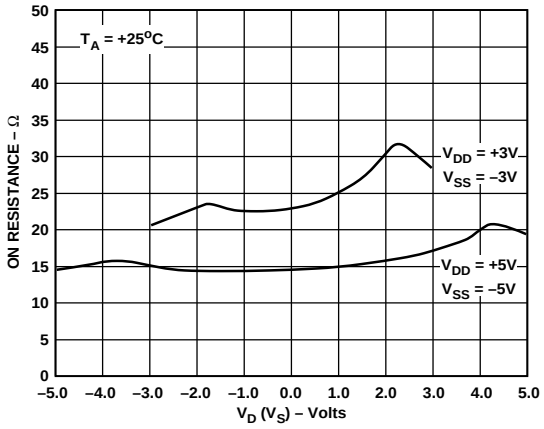


Figure 1. R_{ON} as a Function of V_D (V_S): Dual Supply Voltage

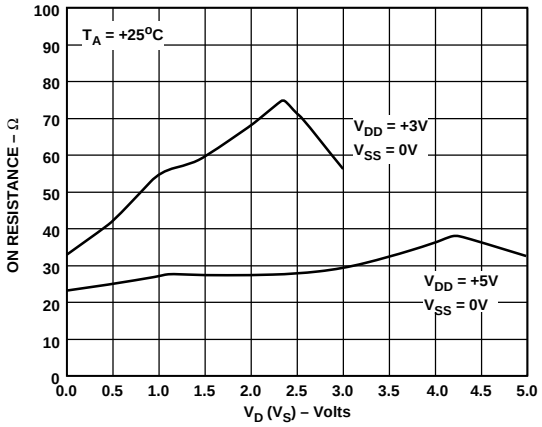


Figure 4. R_{ON} as a Function of V_D (V_S): Single Supply Voltage

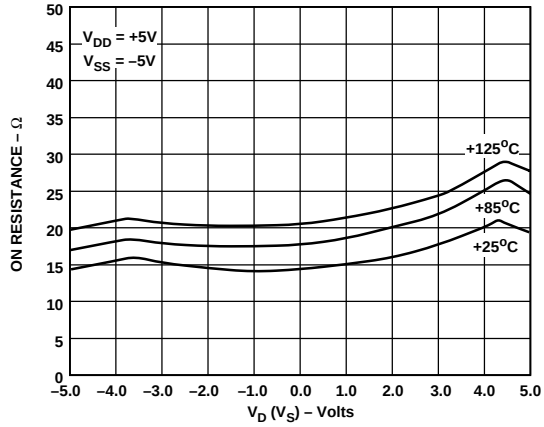


Figure 2. R_{ON} as a Function of V_D (V_S) for Different Temperatures

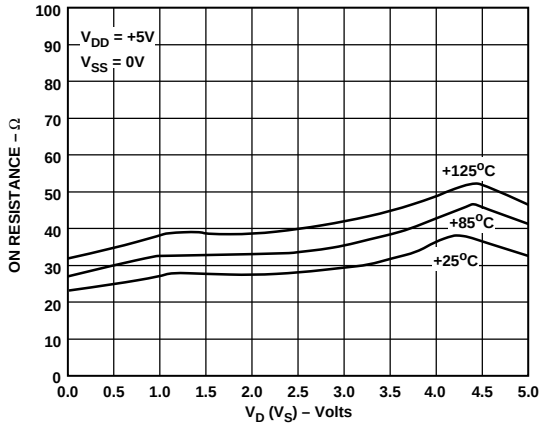


Figure 5. R_{ON} as a Function of V_D (V_S) for Different Temperatures

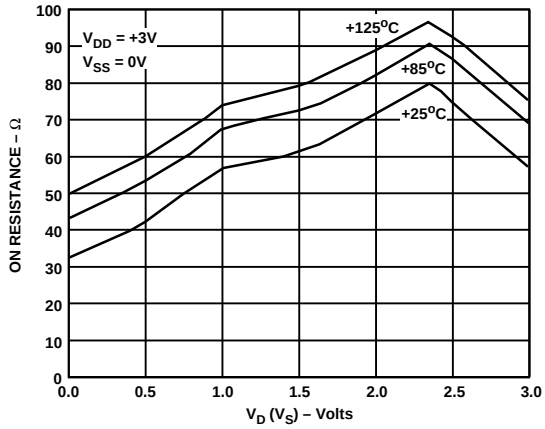


Figure 3. R_{ON} as a Function of V_D (V_S) for Different Temperatures

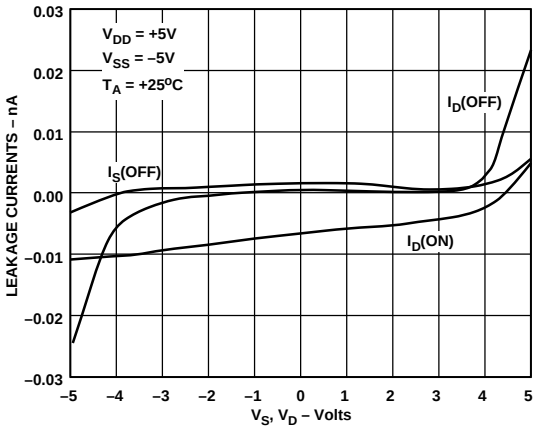


Figure 6. Leakage Currents as a Function of V_D (V_S)

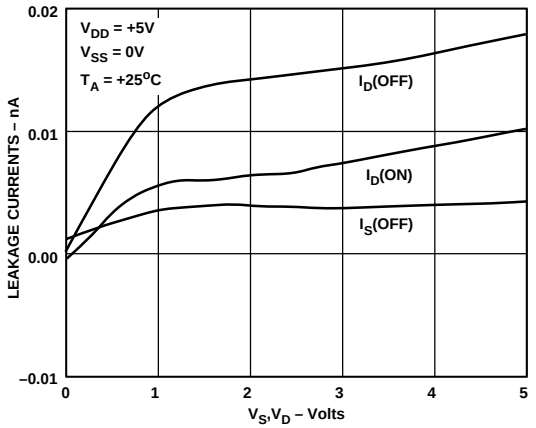


Figure 7. Leakage Currents as a Function of V_D (V_S)

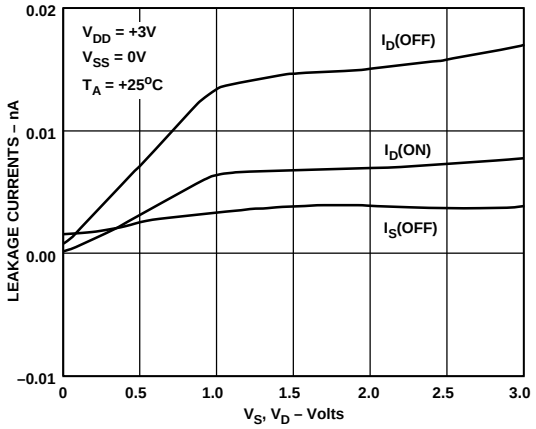


Figure 10. Leakage Currents as a Function of V_D (V_S)

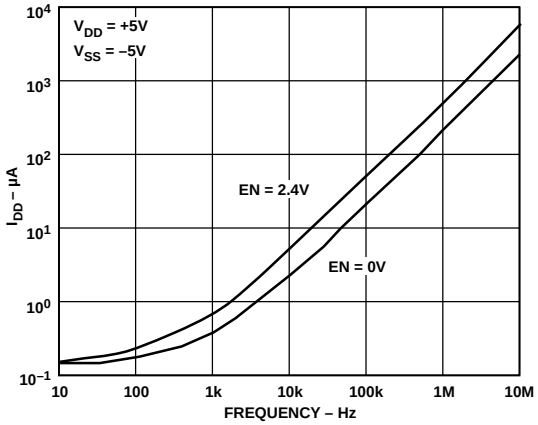


Figure 8. Positive Supply Current vs. Switching Frequency

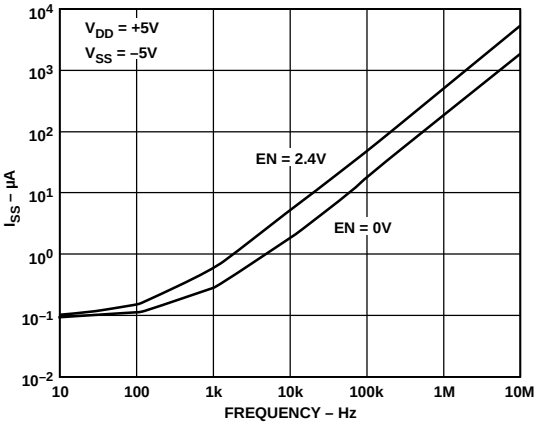


Figure 11. Negative Supply Current vs. Switching Frequency

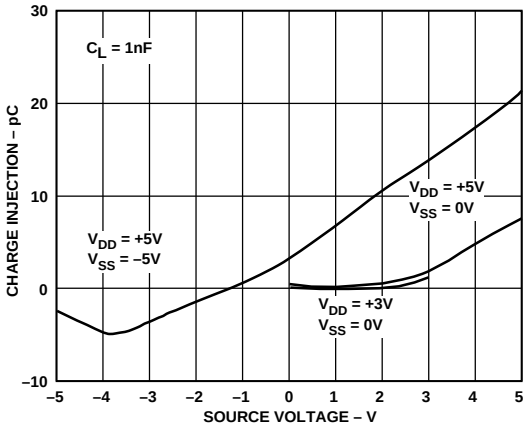


Figure 9. Charge Injection vs. Analog Voltage V_S

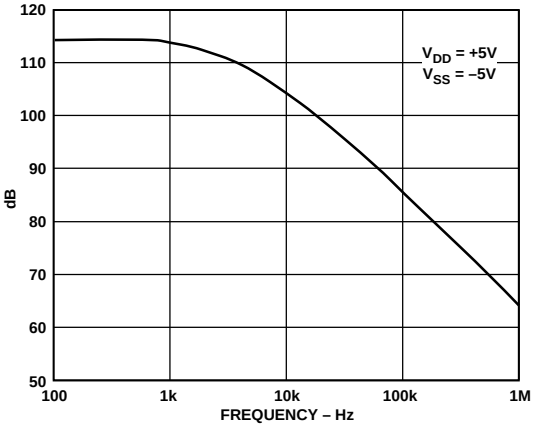
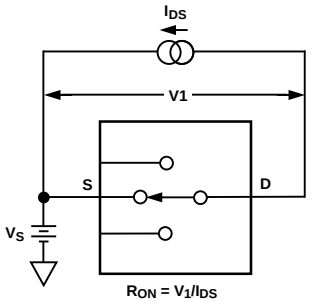
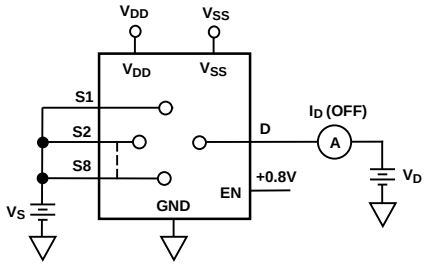


Figure 12. Crosstalk and Off Isolation vs. Frequency

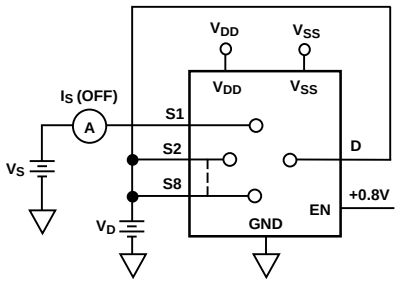
Test Circuits



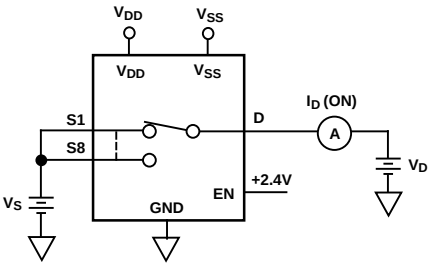
Test Circuit 1. On Resistance



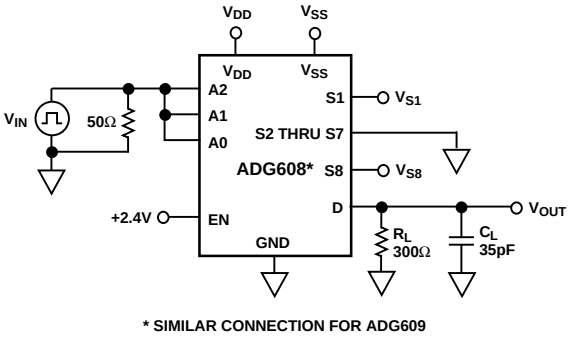
Test Circuit 3. I_D (OFF)

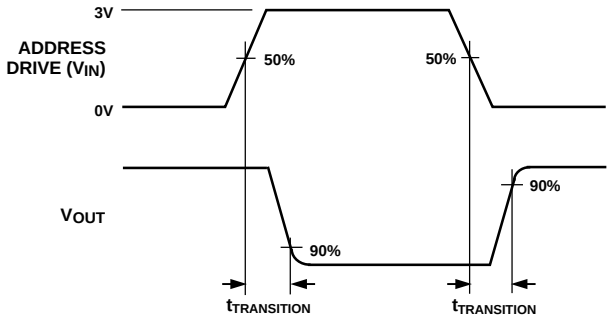


Test Circuit 2. I_S (OFF)

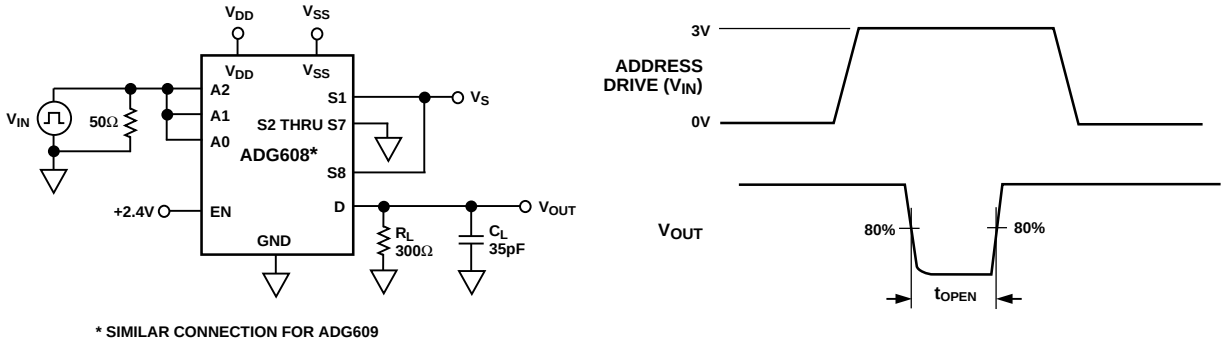


Test Circuit 4. I_D (ON)

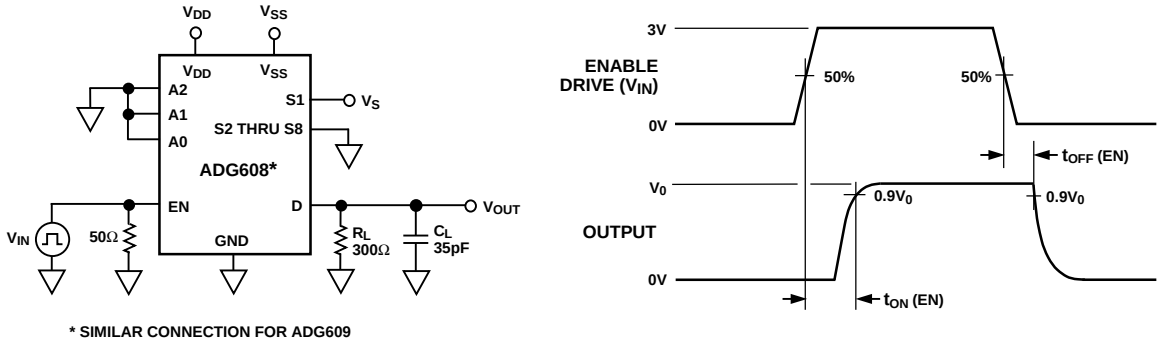




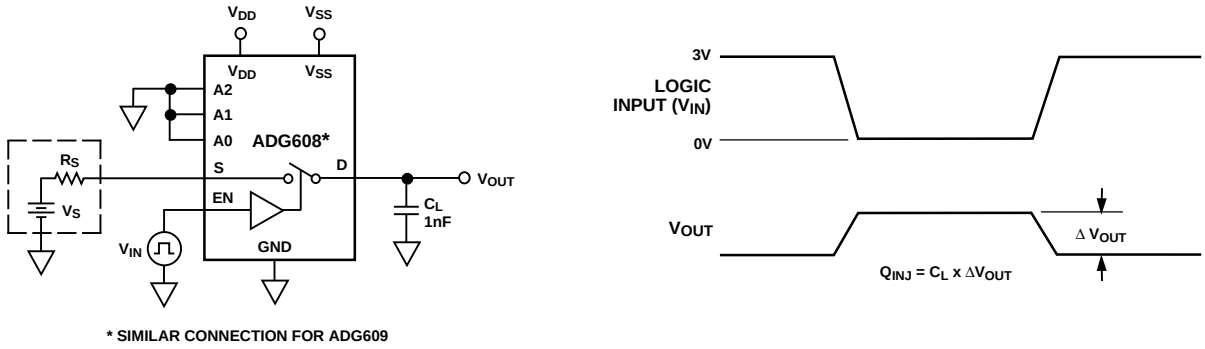
Test Circuit 5. Switching Time of Multiplexer, $t_{TRANSITION}$



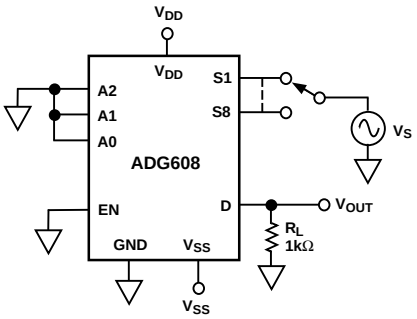
Test Circuit 6. Break-Before-Make Delay, t_{OPEN}



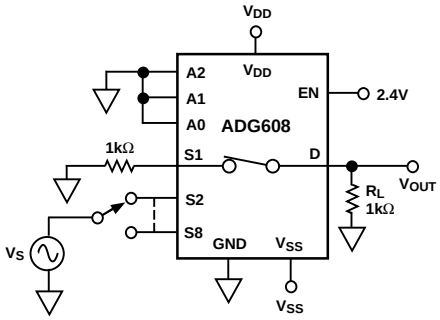
Test Circuit 7. Enable Delay, t_{ON} (EN), t_{OFF} (EN)



Test Circuit 8. Charge Injection



Test Circuit 9. OFF Isolation



Test Circuit 10. Channel-to-Channel Crosstalk

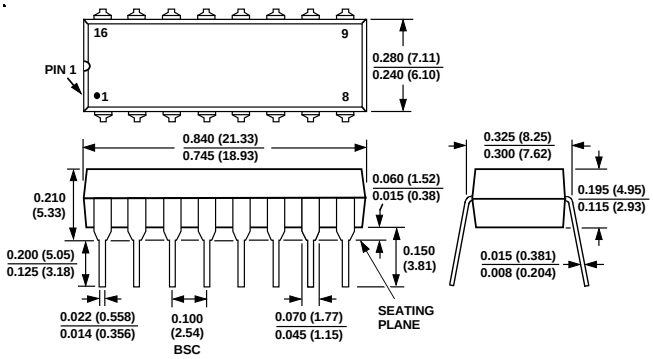
TERMINOLOGY

V_{DD}	Most positive power supply potential.
V_{SS}	Most negative power supply potential in dual supplies. In single supply applications, it may be connected to ground.
GND	Ground (0 V) reference.
R_{ON}	Ohmic resistance between D and S.
ΔR_{ON}	R_{ON} variation due to a change in the analog input voltage with a constant load current.
R_{ON} Match	Difference between the R_{ON} of any two channels.
I_S (OFF)	Source leakage current when the switch is off.
I_D (OFF)	Drain leakage current when the switch is off.
I_D, I_S (ON)	Channel leakage current when the switch is on.
V_D, V_S	Analog voltage on terminals D, S.
C_S (OFF)	Channel input capacitance for "OFF" condition.
C_D (OFF)	Channel output capacitance for "OFF" condition.
C_D, C_S (ON)	"ON" switch capacitance.
C_{IN}	Digital input capacitance.
t_{ON} (EN)	Delay time between the 50% and 90% points of the digital input and switch "ON" condition.
t_{OFF} (EN)	Delay time between the 50% and 90% points of the digital input and switch "OFF" condition.
$t_{TRANSITION}$	Delay time between the 50% and 90% points of the digital inputs and the switch "ON" condition when switching from one address state to another.
t_{OPEN}	"OFF" time measured between the 80% points of both switches when switching from one address state to another.
V_{INL}	Maximum input voltage for logic "0."
V_{INH}	Minimum input voltage for logic "1."
I_{INL} (I_{INH})	Input current of the digital input.
Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an "OFF" channel.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
I_{DD}	Positive supply current.
I_{SS}	Negative supply current.

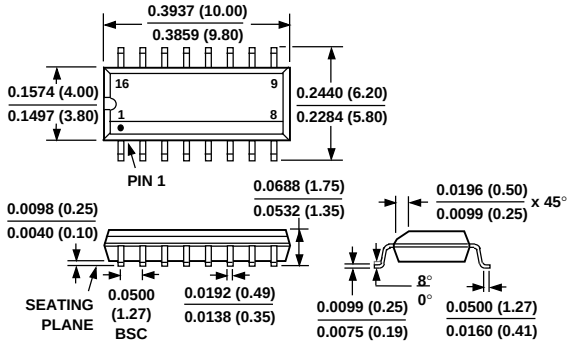
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

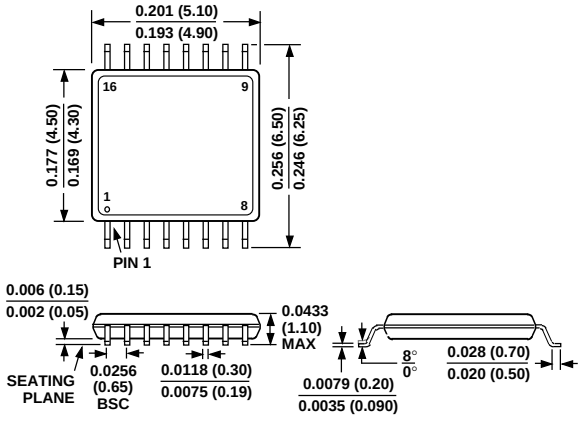
16-Pin Plastic (N-16)



16-Pin SOIC (R-16A)



16-Pin TSSOP (RU-16)



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